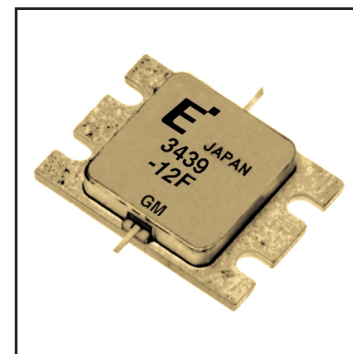


FEATURES

- High Output Power: $P_{1dB} = 41.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 11.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 40\%$ (Typ.)
- Low $IM_3 = -46\text{dBc}$ @ $P_o = 30.5\text{dBm}$
- Broad Band: 3.4 ~ 3.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM3439-12F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ\text{C}$	57.6	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ\text{C}$
Channel Temperature	T_{ch}		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -5.6 mA respectively with gate resistance of 50Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit	
			Min.	Typ.	Max.		
Saturated Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	5800	8700	mA	
Transconductance	g_m	$V_{DS} = 5\text{V}, I_{DS} = 3400\text{mA}$	-	2900	-	mS	
Pinch-off Voltage	V_p	$V_{DS} = 5\text{V}, I_{DS} = 300\text{mA}$	-1.0	-2.0	-3.5	V	
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -300\mu\text{A}$	-5.0	-	-	V	
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10\text{V},$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 3.4 \sim 3.9\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	40.5	41.5	-	dBm	
Power Gain at 1dB G.C.P.	G_{1dB}		10.5	11.5	-	dB	
Drain Current	I_{dsr}		-	3250	3800	mA	
Power-added Efficiency	η_{add}		-	40	-	%	
Gain Flatness	ΔG		-	-	± 0.6	dB	
3rd Order Intermodulation Distortion	IM_3		$f = 3.9\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 30.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}		Channel to Case	-	2.3	2.6	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	ΔT_{ch}	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$	

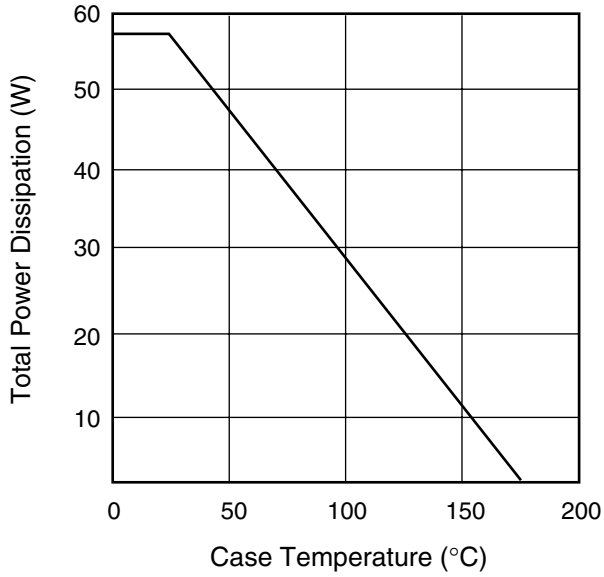
CASE STYLE: IK

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

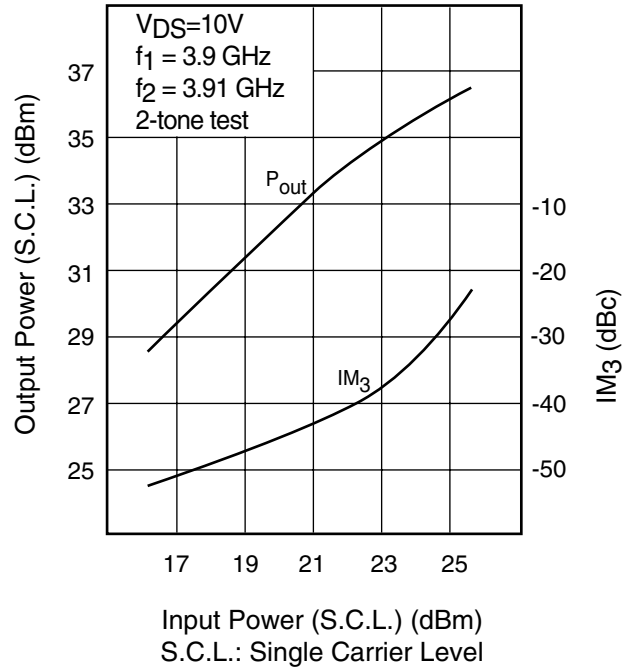
FLM3439-12F

C-Band Internally Matched FET

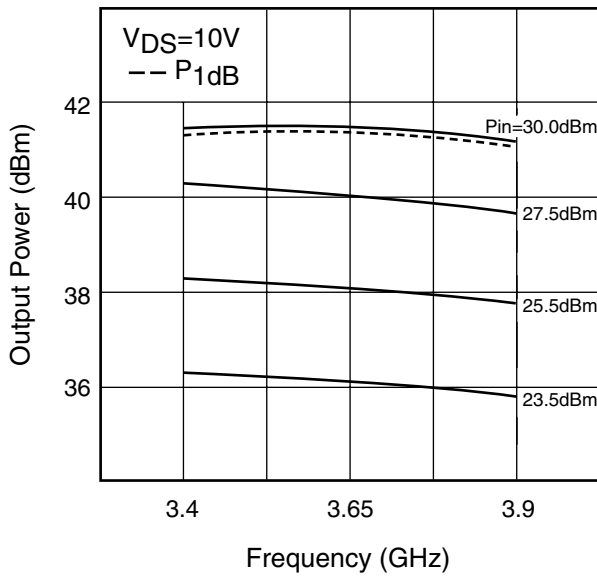
POWER DERATING CURVE



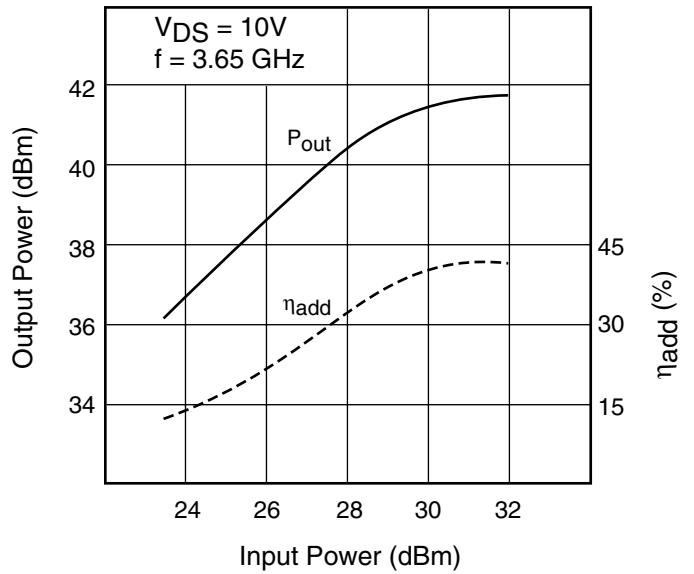
OUTPUT POWER & IM₃ vs. INPUT POWER

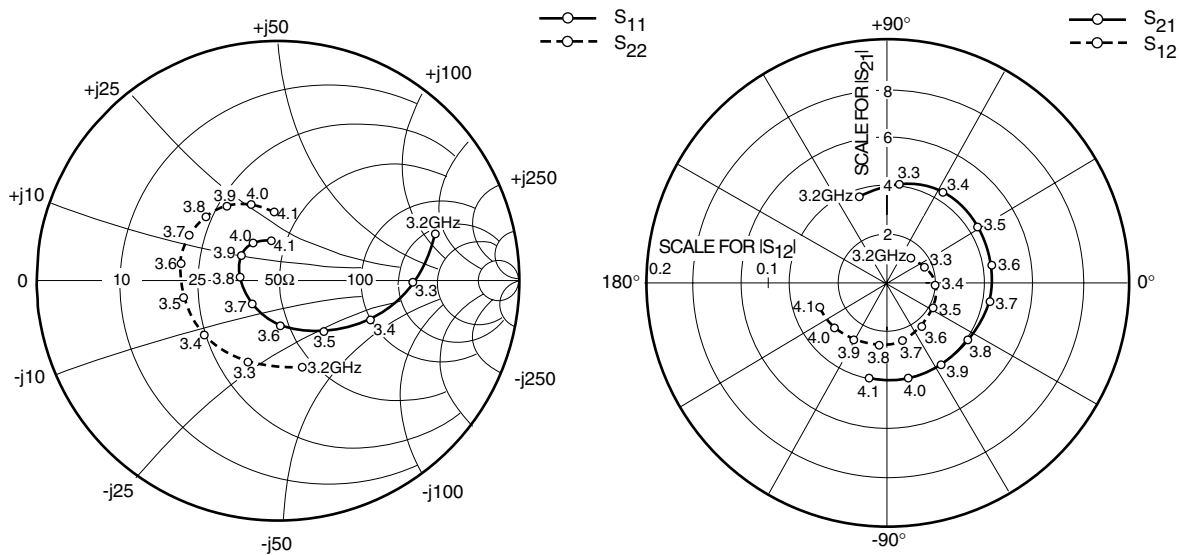


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

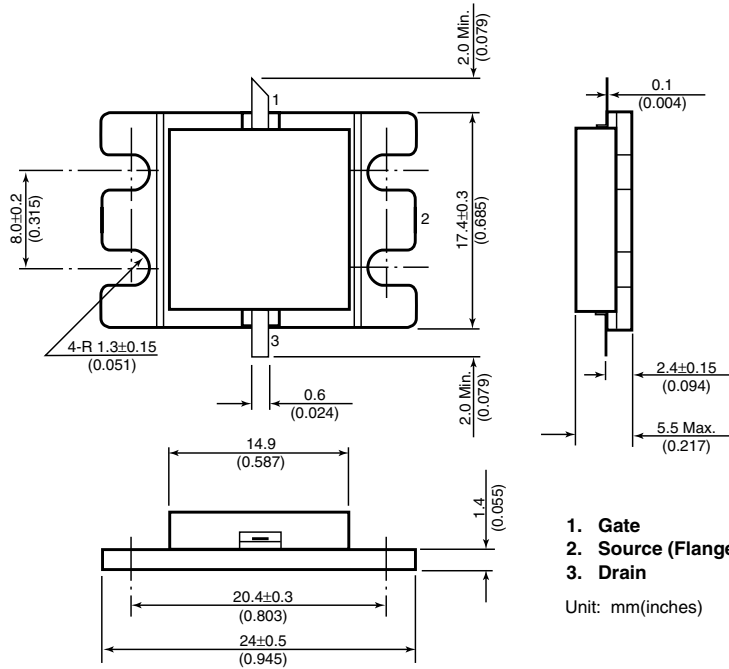
$V_{DS} = 10V, I_{DS} = 3400mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
3200	.683	16.5	3.715	107.6	.028	47.1	.373	-74.2
3300	.559	-1.1	4.086	83.3	.034	23.4	.365	-110.6
3400	.420	-23.1	4.330	57.8	.038	-3.5	.383	-143.1
3500	.287	-48.8	4.423	32.6	.044	-28.7	.403	-169.5
3600	.188	-86.9	4.378	8.7	.047	-51.8	.414	169.9
3700	.143	-137.1	4.282	-14.2	.049	-75.8	.411	153.0
3800	.161	177.8	4.198	-36.0	.052	-97.8	.398	138.2
3900	.183	146.4	4.113	-57.4	.055	-120.1	.374	124.6
4000	.191	123.4	4.050	-78.6	.057	-139.5	.337	110.0
4100	.167	99.4	4.022	-100.2	.059	-160.1	.285	93.1
4200	.106	73.5	4.009	-122.8	.062	177.8	.217	70.1

FLM3439-12F

C-Band Internally Matched FET

Case Style "IK" Metal-Ceramic Hermetic Package



For further information please contact:

Eudyna Devices USA Inc.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
TEL: (408) 232-9500
FAX: (408) 428-9111
www.us.eudyna.com

Eudyna Devices Europe Ltd.

Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte Ltd.

Hong Kong Branch
Rm. 1101, Ocean Centre, 5 Canton Rd.
Tsim Sha Tsui, Kowloon, Hong Kong
TEL: +852-2377-0227
FAX: +852-2377-3921

Eudyna Devices Inc.

Sales Division
1, Kanai-cho, Sakae-ku
Yokohama, 244-0845, Japan
TEL: +81-45-853-8156
FAX: +81-45-853-8170

CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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